

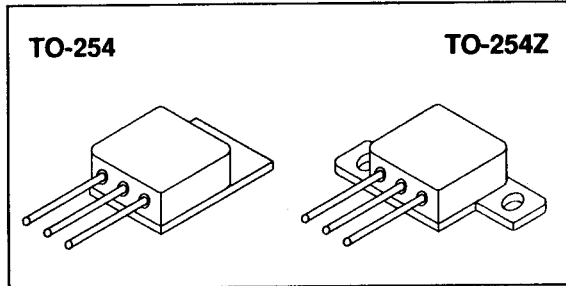
14849 Firestone Boulevard · La Mirada, CA 90638
 Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424

SFF240M
SFF240Z

Designer's Data Sheet

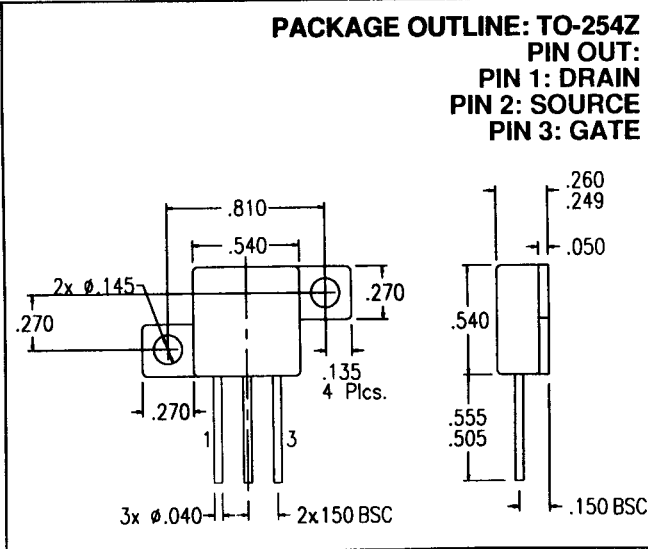
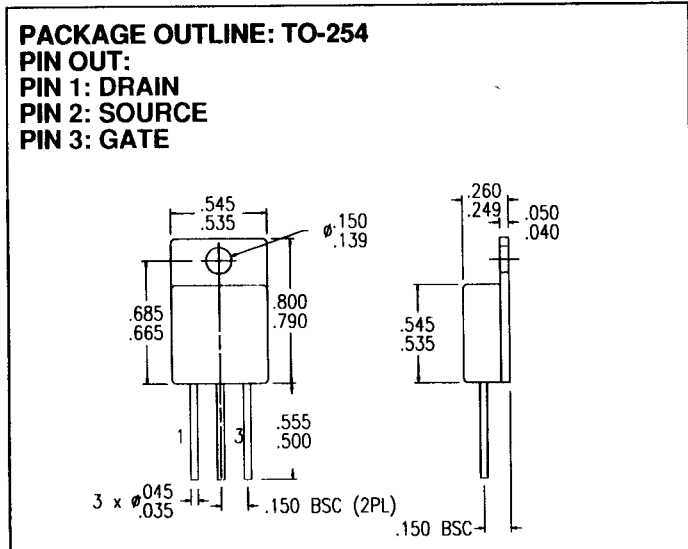
- FEATURES:**
- Rugged construction with polysilicon gate
 - Low RDS(on) and high transconductance
 - Excellent high temperature stability
 - Very fast switching speed
 - Fast recovery and superior dv/dt performance
 - Increased reverse energy capability
 - Low input and transfer capacitance for easy paralleling
 - Ceramic Seals for improved hermeticity
 - Hermetically sealed package
 - TX, TXV and Space Level screening available
 - Replaces: IRFM240 Types

18 AMP
200 VOLTS
0.18Ω
N-CHANNEL
POWER MOSFET



MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	VALUE	UNIT
Drain to Source Voltage	V _{DS}	200	Volts
Gate to Source Voltage	V _{GS}	±20	Volts
Continuous Drain Current	I _D	18	Amps
Operating and Storage Temperature	T _{OP} & T _{STG}	-55 to +150	°C
Thermal Resistance, Junction to Case	R _{θJC}	1.7	°C/W
Total Device Dissipation @ TC=25°C	P _D	74	Watts
Total Device Dissipation @ TC=55°C		56	



Available with Glass or Ceramic Seals. Contact Factory for details.

NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: F00113 B

MED

SFF240M SFF240Z

PRELIMINARY



SOLID STATE DEVICES, INC

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ELECTRICAL CHARACTERISTICS @ T_J=25 C (Unless Otherwise Specified)

RATING		SYMBOL	MIN	TYP	MAX	UNIT
Drain to Source Breakdown Voltage (V _{GS} =0 V, I _D =250μA)		BV _{DSS}	200	---	---	V
Drain to Source on State Resistance (V _{GS} =10 V, I _D = 10 A)		R _{DS(on)}	---	0.13	0.18	Ω
On State Drain Current (V _D > I _{D(on)} X R _{DS(on)} Max, V _{GS} =10 V)		I _{D(on)}	18	---	---	A
Gate Threshold Voltage (V _D =V _{GS} , I _D =250μA)		V _{GS(th)}	2.0	---	4.0	V
Forward Transconductance (V _D ≥ 10 V, I _{DS} = 10 A)		g _{fs}	6.5	10	---	S(Ω)
Zero Gate Voltage Drain Current (V _D =max rated voltage, V _{GS} =0 V) (V _D =80% rated V _D , V _{GS} =0 V, T _A =125°C)		I _{DSS}	---	---	250 1000	μA
Gate to Source Leakage Forward Gate to Source Leakage Reverse	At rated V _{GS}	I _{GSS}	---	---	100 -100	nA
Total Gate Charge Gate to Source Charge Gate to Drain Charge	V _{GS} =10 Volts 80% rated V _D Rated I _D	Q _g Q _{gs} Q _{gd}	---	40 7 21	60 10 32	nC
Turn on Delay Time Rise Time Turn Off Delay Time Fall Time	V _D =50% rated V _D rated I _D R _G = 9.1 Ω R _D = 5.6Ω	t _{d(on)} t _r t _{d(off)} t _f	---	14 52 45 36	21 77 68 54	nsec
Diode Forward Voltage (I _S =rated I _D , V _{GS} =0 V, T _J =25°C)		V _{SD}	---	---	2.0	V
Diode Reverse Recovery Time Reverse Recovery Charge	T _J =25°C I _F =rated I _D di/dt=100 A/μsec	t _{rr} Q _{RR}	120 1.3	250 2.6	530 5.6	nsec μC
Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{GS} =0 Volts V _D =25 Volts f= 1 MHz	C _{iss} C _{oss} C _{rss}	---	1300 380 93	---	pF

SAFE OPERATING AREA (S.O.A.)
T_C = 25 C, D.C. CONDITION

